

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (***Currently Amended***): A chemical-mechanical-polishing slurry composition for polishing and ablating an oxide layer selectively in relation to a nitride layer, the chemical-mechanical-polishing slurry composition comprising:

ceria polishing particles;

a dispersing agent; and

an anionic additive,

wherein the anionic additive is added to control a concentration of the anionic additive so that a polishing-rate selection ratio of an oxide layer to a nitride layer is 40 : 1 or greater, [[and]]

the ceria polishing particles are polyhedron,

a particle size of the ceria polishing particles is within a range from 148 nm to 290 nm,

the ceria polishing particles are polycrystalline particles of which grain boundaries are 100 nm or larger,

the anionic additive is water-soluble polyacrylic acid or water-soluble polycarboxylate, and

a concentration of the anionic additive is from 0.1 to 0.6 wt% in relation to the entirety of the slurry composition.

2.-5. (***Cancelled***)

6. **(Currently Amended):** A method for planarizing a surface of a semiconductor device comprising:

preparing a semiconductor substrate in which a level difference is formed on a surface thereof and a nitride layer is formed at least on an upper level surface of the level difference;

depositing an oxide layer which is for filling the level difference and planarizing the surface of the semiconductor substrate so that a predetermined thickness of the oxide layer can be added to a surface of the nitride layer; [[and]]

ablating the oxide layer by using a silica slurry before the surface of the nitride layer is exposed; and

ablating the oxide layer by a chemical-mechanical-polishing process so as to expose the surface of the nitride layer,

wherein in the chemical-mechanical-polishing process, a chemical-mechanical-polishing slurry composition is used, and

the chemical-mechanical-polishing slurry composition includes ceria polishing particles, a dispersing agent, and an anionic additive, in which the anionic additive is added to control a concentration of the anionic additive so that a polishing-rate selection ratio of an oxide layer to a nitride layer is 40 : 1 or greater,

the ceria polishing particles are polyhedron, [[and]]

a particle size of the ceria polishing particles is within a range from 148 nm to 290 nm,

the ceria polishing particles are polycrystalline particles of which grain boundaries are 100 nm or larger,

the anionic additive is water-soluble polyacrylic acid or water-soluble polycarboxylate,

a concentration of the anionic additives is from 0.1 to 0.6 wt% in relation to the entirety of the slurry composition,

the polishing conditions are controlled such that the zeta potential on the surface of the oxide layer becomes a negative value and the zeta potential on the surface of the nitride layer becomes a positive value, and

the oxide layer is a silicon oxide layer, and the nitride layer is a silicon nitride layer.

7. **(Previously Presented)**: The method for planarizing a surface of a semiconductor device according to Claim 6,

wherein the level difference is a trench area formed on the surface of the semiconductor substrate.

8.-12. **(Cancelled)**

13. **(Currently Amended)**: A method for controlling a selection ratio of a chemical-mechanical-polishing slurry composition for polishing and ablating an oxide layer selectively in relation to a nitride layer, the method comprising:

confirming a selection ratio of an oxide layer to a nitride layer of a chemical-mechanical-polishing slurry composition which includes ceria polishing particles, a dispersing agent, and an anionic additive, while a concentration of the anionic additive is changed; [[and]]

confirming the polishing-rate selection ratio of the oxide layer to the nitride layer, while a particle size of the ceria polishing particles is changed; and

adjusting the concentration of the anionic additive to attain a desired selection ratio of the slurry composition, on the basis of the confirmed polishing-rate selection ratio, thereby controlling the selection ratio of the slurry composition,

wherein the ceria polishing particles are polyhedron, [[and]]

the particle size of the ceria polishing particles is within a range from 148 nm to 290 nm,

the ceria polishing particles are polycrystalline particles of which grain boundaries are 100 nm or larger,

the anionic additive is water-soluble polyacrylic acid or water-soluble polycarboxylate,

the concentration of the anionic additive is from 0.1 to 0.6 wt% in relation to the entirety of the slurry composition, and

14.-17. (*Cancelled*)

18. (*New*): The chemical-mechanical-polishing slurry composition according to claim 1,

wherein the particle size of the ceria polishing particles is about 148 nm or about 290nm, and

the dispersing agent is poly-metha-acrylic ammonium salt.

19. (*New*): The method for planarizing a surface of a semiconductor device according to claim 6,

wherein the particle size of the ceria polishing particles is about 148 nm or about 290nm, and

the dispersing agent is poly-metha-acrylic ammonium salt.

20. (*New*): The method for controlling a selection ratio of a chemical-mechanical-polishing slurry composition according to Claim 13,

wherein the particle size of the ceria polishing particles is about 148 nm or about 290nm, and

the dispersing agent is poly-metha-acrylic ammonium salt.